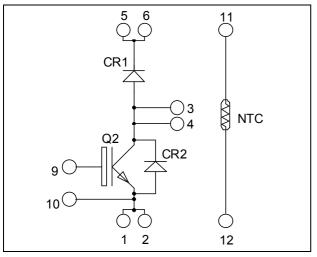
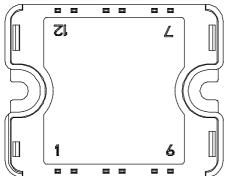


Boost chopper Trench + Field Stop IGBT3 **Power Module**





Pins 1/2; 3/4; 5/6 must be shorted together

Maximum Power Dissipation Reverse Bias Safe Operating Area

Absolute maximum ratings

PD

RBSOA

Symbol Parameter Max ratings Unit Collector - Emitter Breakdown Voltage 600 **V**_{CES} V $T_C = 25^{\circ}C$ 225 * I_C Continuous Collector Current $T_C = 80^{\circ}C$ 150 * A Pulsed Collector Current $T_C = 25^{\circ}C$ 350 I_{CM} Gate – Emitter Voltage ±20 V V_{GE}

11	Application

- AC and DC motor control
- Switched Mode Power Supplies

 $V_{CES} = 600V$

Power Factor Correction

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation .
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting

480

300A @ 550V

- Low profile
- **RoHS** Compliant

 $T_C = 25^{\circ}C$

 $T_i = 150^{\circ}C$

Specification of IGBT device but output current must be limited to 75A to not exceed a delta of temperature greater than 30°C for the connectors.

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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APTGT150DA60T1G

 $I_C = 150A^*$ @ $Tc = 80^{\circ}C$



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified · · ·

Electri	cal Characteristics	1				
Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	μA
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $T_j = 25^{\circ}C$		1.5	1.9	V
V _{CE(sat)}	Conector Enlitter Saturation Voltage	$I_{\rm C} = 150 \text{A} \qquad T_{\rm j} = 150^{\circ} \text{C}$		1.7		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5 \text{ mA}$	5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		9200		
C _{oes}	Output Capacitance	$V_{CE} = 25V$		580		pF
Cres	Reverse Transfer Capacitance	f = 1 MHz		270		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)		115		
T _r	Rise Time	$V_{GE} = \pm 15V$		45		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 150A$		225		ns
T _f	Fall Time	$R_G = 3.3\Omega$		55		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C)		130		
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$		50		ns
T _{d(off)}	Turn-off Delay Time	$I_{\rm C} = 150 {\rm A}$		300		115
T _f	Fall Time	$R_G = 3.3\Omega$		70		
Б		$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		0.85		mJ
Eon	Turn on Energy	$V_{Bus} = 300V$ $T_j = 150^{\circ}C$		1.5		111J
E	Turn off Energy	$I_{\rm C} = 150 {\rm A}$ $T_{\rm j} = 25^{\circ} {\rm C}$		4.1		mJ
Loff	E_{off} Turn off Energy $R_G = 3.3\Omega$	$R_G = 3.3\Omega$ $T_j = 150^{\circ}C$		5.3		1113

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			250 500	μΑ
I _F	DC Forward Current		$Tc = 80^{\circ}C$		150		А
$V_{\rm F}$	Diode Forward Voltage	$I_{\rm F} = 150 {\rm A}$	$T_j = 25^{\circ}C$		1.6	2	V
▼ F		$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.5		v
+	t _{rr} Reverse Recovery Time		$T_j = 25^{\circ}C$		130		ns
ι _{rr}			$T_{j} = 150^{\circ}C$		225		115
0	Q _{rr} Reverse Recovery Charge	$I_{\rm F} = 150 \text{A}$ $V_{\rm R} = 300 \text{V}$	$T_j = 25^{\circ}C$		6.9		
Qrr		$v_{\rm R} = 300 v$ di/dt = 3000 A/µs	$T_{i} = 150^{\circ}C$		14.5		μC
Б	Reverse Recovery Energy		$T_j = 25^{\circ}C$		1.6		mI
Er			$T_{j} = 150^{\circ}C$		3.5		mJ

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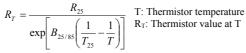
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Thermal and package characteristics

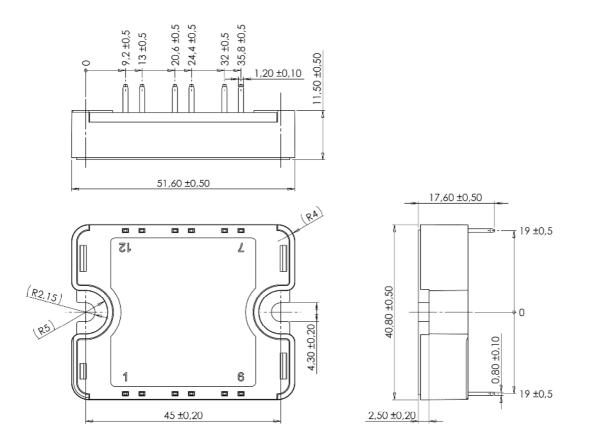
Symbol	ol Characteristic		Min	Тур	Max	Unit	
P	Junction to Case Thermal Resistance		IGBT			0.31	°C/W
R _{thJC} Junction to Case Thermal Resistance			Diode			0.52	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
T _J	Operating junction temperature range		-40		175		
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K



SP1 Package outline (dimensions in mm)



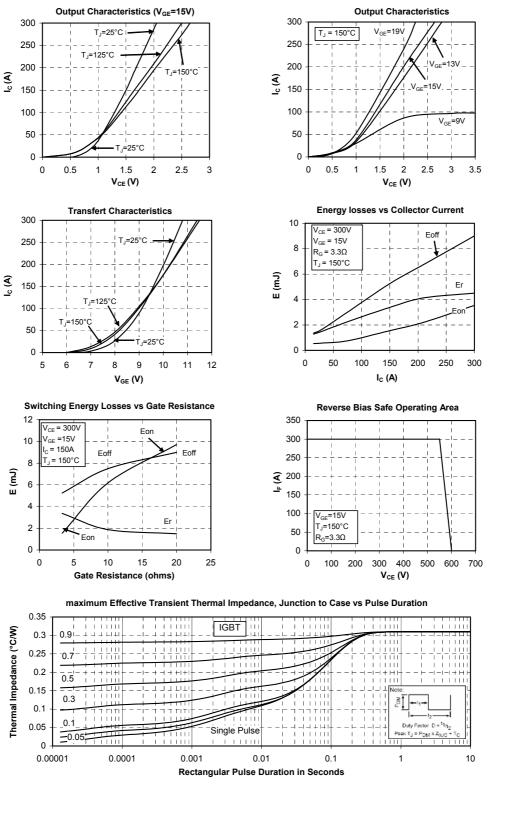
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

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3 - 6



Typical Performance Curve



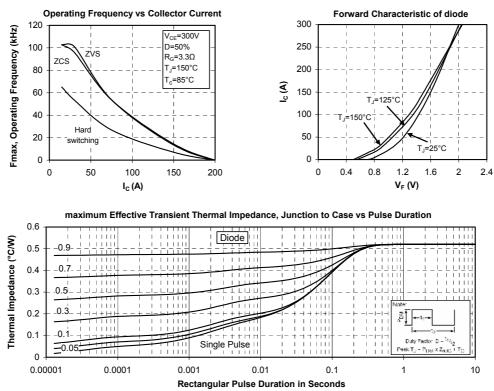
APTGT150DA60T1G-Rev 1 October, 2012

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